# MOSFET – Single, N-Channel with ESD Protection, Small Signal, SC-75 and SC-89 20 V, 915 mA

#### **Features**

- Low R<sub>DS(on)</sub> Improving System Efficiency
- Low Threshold Voltage, 1.5 V Rated
- ESD Protected Gate
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available

#### **Applications**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Portables like Cell Phones, PDAs, Digital Cameras, Pagers, etc.

#### MAXIMUM RATINGS (T<sub>.J</sub> = 25°C unless otherwise stated)

		,			
Parame	Symbol	Value	Units		
Drain-to-Source Voltage	$V_{DSS}$	20	V		
Gate-to-Source Voltage			$V_{GS}$	±6.0	V
Continuous Drain	Steady	T <sub>A</sub> = 25°C	I <sub>D</sub>	915	mA
Current (Note 1)	Current (Note 1) State $T_A = 85^{\circ}C$			660	
Power Dissipation (Note 1)	Stea	dy State	P <sub>D</sub>	300	mW
Pulsed Drain Current	t <sub>p</sub> =	=10 μs	I <sub>DM</sub>	1.3	Α
Operating Junction and St	T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C		
Continuous Source Currer	I <sub>S</sub>	280	mA		
Lead Temperature for Solo (1/8" from case for 10 s)	TL	260	°C		

# THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Units
Junction-to-Ambient - Steady State (Note 1) SC-75 / SOT-416	$R_{\theta JA}$	416	°C/W
SC-89		400	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

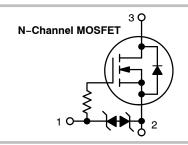
 Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



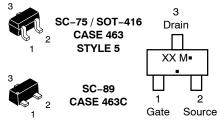
# ON Semiconductor®

#### http://onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> MAX
20 V	0.127 Ω @ 4.5 V	
	0.170 Ω @ 2.5 V	915 mA
	0.242 Ω @ 1.8 V	01011111
	0.500 Ω @ 1.5 V	



# MARKING DIAGRAM & PIN ASSIGNMENT



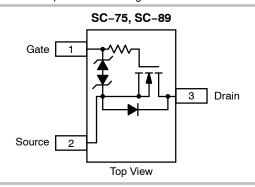
XX = Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.



## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 4 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Test Cond	dition	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•		•		•		
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	26		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>				18.4		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V, V_{E}$	<sub>OS</sub> = 16 V			100	nA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub>	<sub>S</sub> = ±4.5 V			±1.0	μΑ
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D}$	= 250 μΑ	0.45	0.76	1.1	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				-2.15		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D$	= 600 mA		127	230	mΩ
		$V_{GS} = 2.5 \text{ V}, I_D$	= 500 mA		170	275	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub>	= 350 mA		242	700	
		V <sub>GS</sub> = 1.5 V, I <sub>D</sub> = 40 mA			500 950	950	
Forward Transconductance	9FS	$V_{DS} = 10 \text{ V}, I_D$	= 400 mA		1.4		S
CHARGES AND CAPACITANCES							
Input Capacitance	C <sub>ISS</sub>				110		pF
Output Capacitance	C <sub>OSS</sub>	$V_{GS} = 0 \text{ V, f} = V_{DS} = 1$			16		7
Reverse Transfer Capacitance	C <sub>RSS</sub>	100			12		
Total Gate Charge	Q <sub>G(TOT)</sub>				1.82		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	$V_{GS} = 4.5 \text{ V}, V_{I}$	<sub>DS</sub> = 10 V,		0.2		
Gate-to-Source Charge	$Q_{GS}$	$I_D = 0.2$	Ā		0.3		
Gate-to-Drain Charge	$Q_{GD}$				0.42		
SWITCHING CHARACTERISTICS (No	te 3)						
Turn-On Delay Time	t <sub>d(ON)</sub>				3.7		ns
Rise Time	t <sub>r</sub>	$V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, $I_{D}$ = 0.2 A, $R_{G}$ = 10 $\Omega$			4.4		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				25		
Fall Time	t <sub>f</sub>				7.6		
DRAIN-SOURCE DIODE CHARACTE	RISTICS		•		-		_
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25°C		0.67	1.1	V
	I <sub>S</sub> = 200 mA	T <sub>J</sub> = 125°C		0.54			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width  $\leq 300 \ \mu s$ , duty cycle  $\leq 2\%$ .

<sup>3.</sup> Switching characteristics are independent of operating junction temperatures.

## TYPICAL ELECTRICAL CHARACTERISTICS

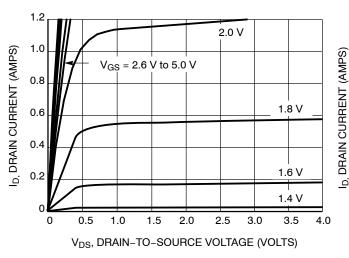
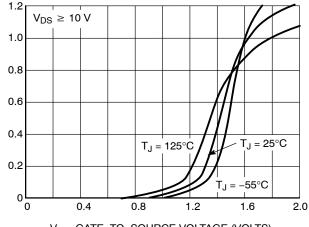


Figure 1. On-Region Characteristics



 $V_{GS}$ , GATE-TO-SOURCE VOLTAGE (VOLTS) Figure 2. Transfer Characteristics

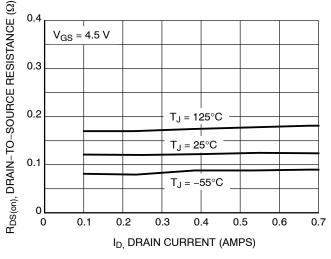


Figure 3. On-Resistance vs. Drain Current and Temperature

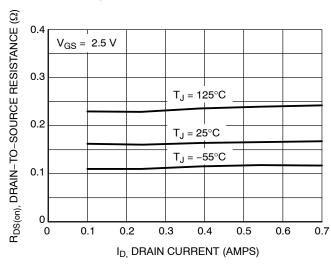


Figure 4. On-Resistance vs. Drain Current and Temperature

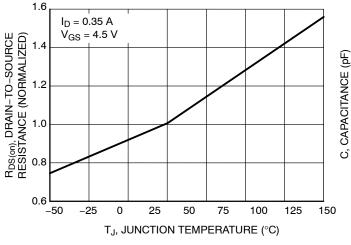


Figure 5. On–Resistance Variation with Temperature

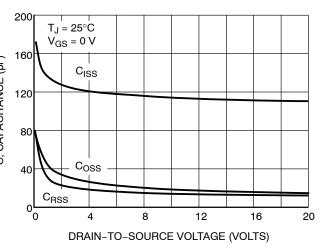


Figure 6. Capacitance Variation

## TYPICAL ELECTRICAL CHARACTERISTICS

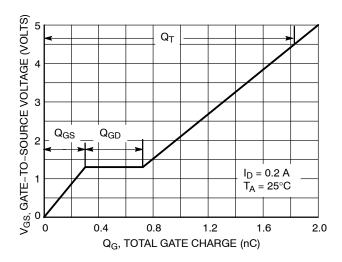


Figure 7. Gate-to-Source Voltage vs. Total Gate Charge

Figure 8. Diode Forward Voltage vs. Current

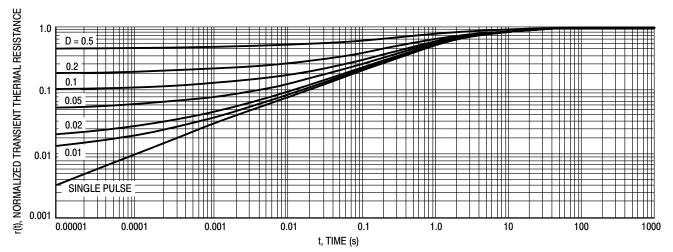


Figure 9. Normalized Thermal Response

#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
NTA4153NT1	TR	SC-75 / SOT-416	3000 / Tape & Reel
NTA4153NT1G	TR	SC-75 / SOT-416 (Pb-Free)	3000 / Tape & Reel
NTE4153NT1G	TP	SC-89 (Pb-Free)	3000 / Tape & Reel
NVA4153NT1G	VR	SC-75 / SOT-416 (Pb-Free)	3000 / Tape & Reel
NVE4153NT1G	VP	SC-89 (Pb-Free)	3000 / Tape & Reel

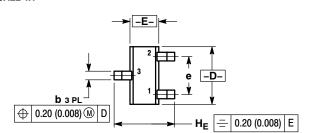
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

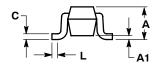




SC-75/SOT-416 **CASE 463 ISSUE G** 

**DATE 07 AUG 2015** 





STYLE 1: PIN 1. BASE 2. EMITTER STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. COLLECTOR 3. CATHODE STYLE 4: STYLE 5: PIN 1. CATHODE 2. CATHODE PIN 1. GATE 2. SOURCE

3. DRAIN

# **GENERIC MARKING DIAGRAM\***

3. ANODE



XX = Specific Device Code Μ = Date Code

= Pb-Free Package

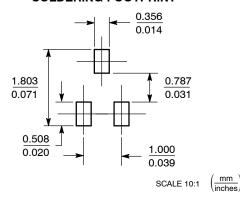
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC				0.04 BSC	)
L	0.10	0.15	0.20	0.004	0.006	0.008
He	1.50	1.60	1.70	0.060	0.063	0.067

# RECOMMENDED **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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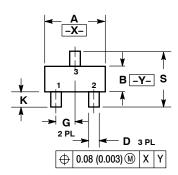
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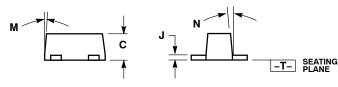


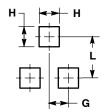


SC-89, 3 LEAD CASE 463C-03 **ISSUE C** 

**DATE 31 JUL 2003** 







RECOMMENDED PATTERN OF SOLDER PADS

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- 463C-01 OBSOLETE, NEW STANDARD 463C-02.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.60	1.70	0.059	0.063	0.067
В	0.75	0.85	0.95	0.030	0.034	0.040
С	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
Н	C	.53 REF	=	0	.021 RE	F
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1	1.10 REF			.043 RE	F
M			10			10
N			10 -			10 -
S	1.50	1.60	1.70	0.059	0.063	0.067

# **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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